





60V PNP HIGH PERFORMANCE TRANSISTOR IN SOT223

Features

- BV_{CEO} > -60V
- I_C = -3A High Continuous Current
- I_{CM} = -6A Peak Pulse Current
- Low Saturation Voltage V_{CE(sat)} < -300mV @ -1A
- Complementary NPN Type: FZT651
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound;
 UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 (23)
- Weight: 0.112 grams (Approximate)

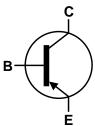
Applications

- Automotive Lighting
- MOSFET and IGBT Gate Driving

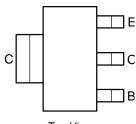
SOT223



Top View



Device Symbol



Top View Pin-Out

Ordering Information (Note 4)

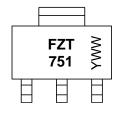
Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
FZT751TA	AEC-Q101	FZT751	7	12	1,000
FZT751TC	AEC-Q101	FZT751	13	12	4,000

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

SOT223



FZT 751 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 5= 2015) WW or $\overline{W}W$ = Week Code (01~53)





Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-80	V
Collector-Emitter Voltage	V_{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-7	V
Continuous Collector Current	Ic	-3	Α
Peak Pulse Current	I _{CM}	-6	Α

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	0	2	W
Power Dissipation	(Note 6)	─ P _D	3	W
Thermal Resistance, Junction to Ambient	(Note 5)	D	62.5	°C/W
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{\theta JA}$	41.7	°C/W
Thermal Resistance, Junction to Leads (Note 7)		$R_{ heta JL}$	12.9	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

ESD Ratings (Note 8)

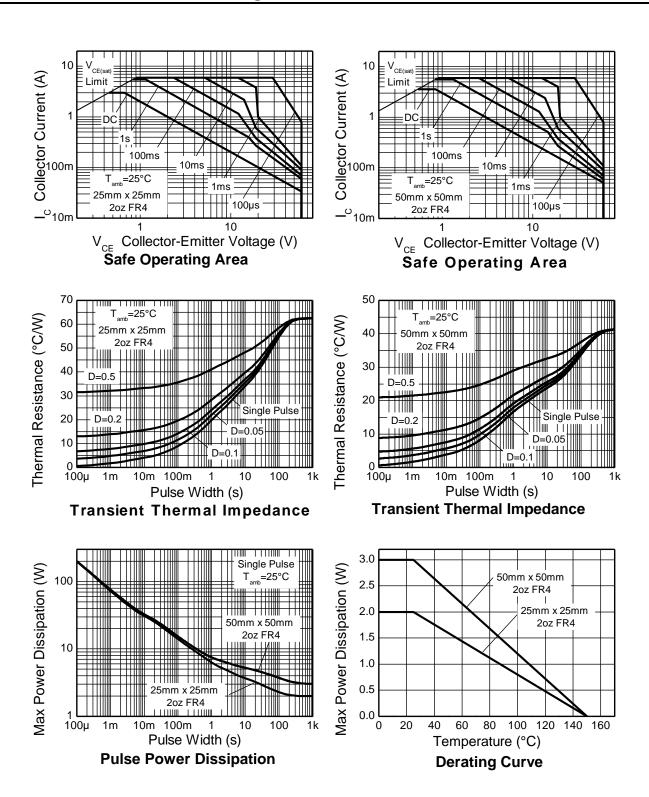
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes

- 5. For a device mounted with the collector lead on 25mm x 25mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in steady-state.
- 6. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 8. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



Thermal Characteristics and Derating Information







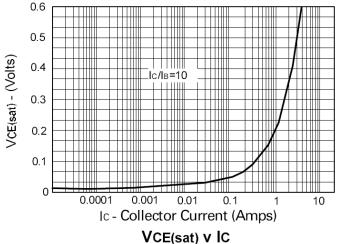
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

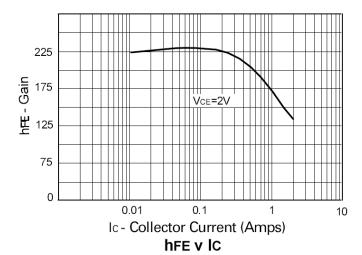
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV _{CBO}	-80	_	_	V	$I_{C} = -100 \mu A$
Collector-Emitter Breakdown Voltage (Note 9)	BV _{CEO}	-60	_	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	_	-	V	$I_E = -100 \mu A$
Collector Cut-Off Current	I _{CBO}	-	<1	-100	nA	$V_{CB} = -60V$
Collector Cut-Oir Current		-	_	-10	μΑ	$V_{CB} = -60V$, $T_{amb} = +100$ °C
Emitter Cut-Off Current	I _{EBO}	-	<1	-100	nA	$V_{EB} = -4V$
Collector-Emitter Saturation Voltage (Note 9)	V	-	-0.15	-0.3	V	$I_C = -1A$, $I_B = -100mA$
Collector-Entitler Saturation Voltage (Note 9)	V _{CE(sat)}	-	-0.45	-0.6	V	$I_C = -3A$, $I_B = -300mA$
Base-Emitter Saturation Voltage (Note 9)	V _{BE(sat)}	_	-0.9	-1.25	V	$I_C = -1A$, $I_B = -100mA$
Base-Emitter Turn-On Voltage (Note 9)	V _{BE(on)}	-	-0.8	-1.0	V	$I_C = -1A$, $V_{CE} = -2V$
	h _{FE}	70	200	_		$I_C = -50 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Coin (Note 0)		100	200	300		$I_C = -500 \text{mA}, V_{CE} = -2 \text{V}$
DC Current Gain (Note 9)		80	170	-	_	$I_C = -1A$, $V_{CE} = -2V$
		40	150	_		I _C = -2A, V _{CE} = -2V
Current Gain-Bandwidth Product	f⊤	100	140	-	MHz	V _{CE} = -5V, I _C = -100mA f = 100MHz
Turn-On Time	t _{on}	-	40	_	ns	$V_{CC} = -10V, I_C = -500mA$
Turn-Off Time	t _{off}	-	450	_	ns	$I_{B1} = I_{B2} = -50 \text{mA}$
Output Capacitance	C _{obo}	-	-	30	pF	$V_{CB} = -10V$, $f = 1MHz$

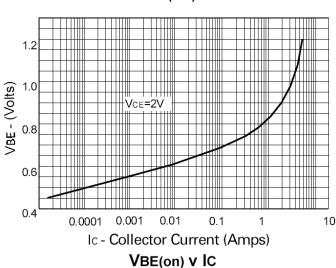
Note: 9. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.

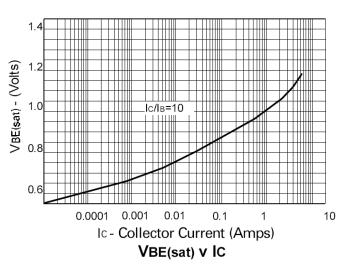


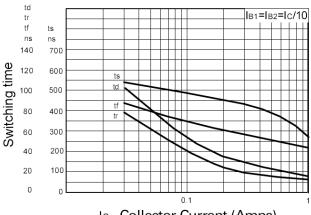
Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)









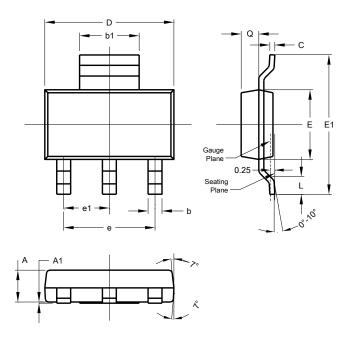






Package Outline Dimensions

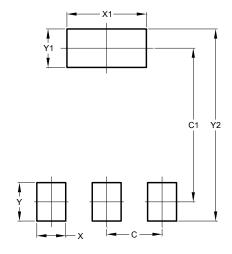
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



SOT223						
Dim	Min	Max	Тур			
Α	1.55	1.65	1.60			
A1	0.010	0.15	0.05			
b	0.60	0.80	0.70			
b1	2.90	3.10	3.00			
С	0.20	0.30	0.25			
D	6.45	6.55	6.50			
Е	3.45	3.55	3.50			
E1	6.90	7.10	7.00			
е	-	-	4.60			
e1	-	-	2.30			
L	0.85	1.05	0.95			
Q	0.84	0.94	0.89			
All [All Dimensions in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.30
C1	6.40
Х	1.20
X1	3.30
Υ	1.60
Y1	1.60
Y2	8.00





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